

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

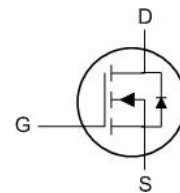
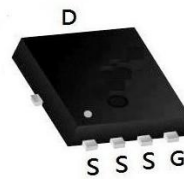
### Description

The XXW80N02F is the high cell density trenched N-ch MOSFETs, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications. The XXW80N02F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
20V	3.5 mΩ	80A

### PDFN5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	80	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	35	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	200	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	58	mJ
I <sub>AS</sub>	Avalanche Current	41	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	58	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	2.6	°C/W

**N-Ch 20V Fast Switching MOSFETs**  
**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

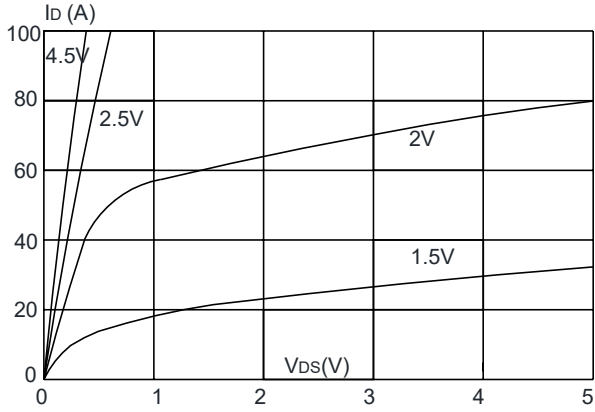
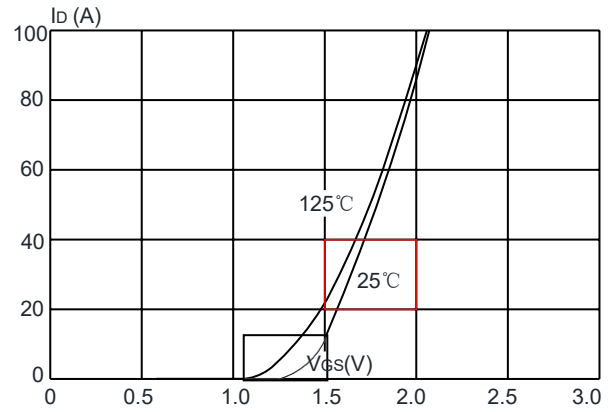
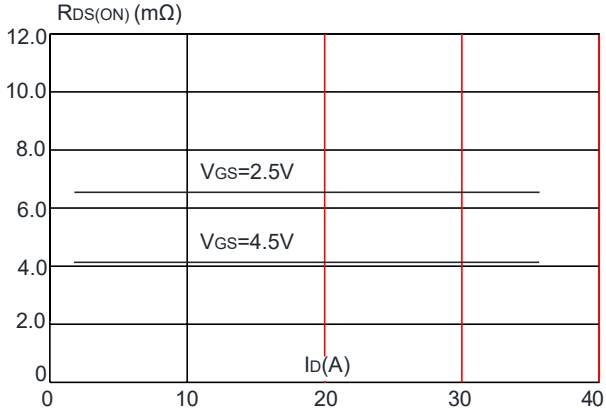
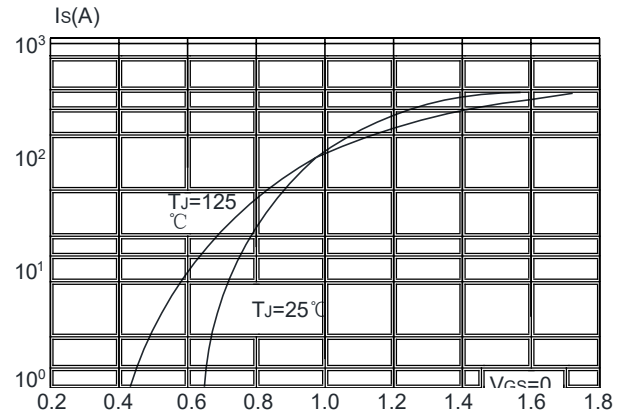
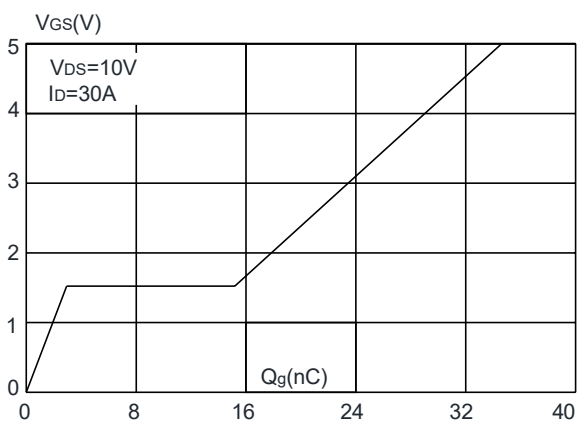
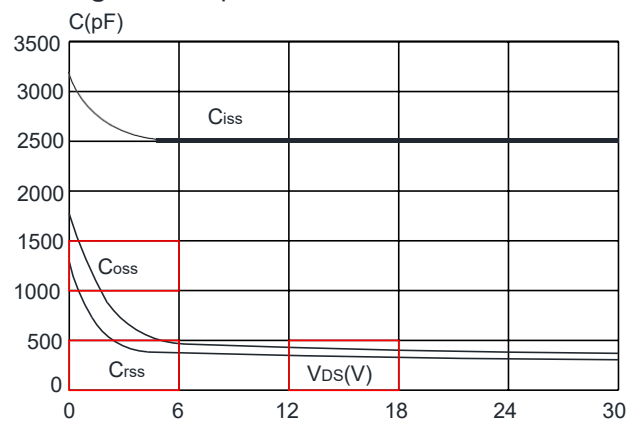
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1.1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=4.5V, I_D=30A$	-	3.5	5	m $\Omega$
		$V_{GS}=2.5V, I_D=20A$	-	6.5	9	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f = 1.0MHz$	-	2500	-	pF
$C_{oss}$	Output Capacitance		-	407	-	pF
$C_{riss}$	Reverse Transfer Capacitance		-	386	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=30A,$ $V_{GS}=4.5V$	-	32	-	nC
$Q_{gs}$	Gate-Source Charge		-	3	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	11	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=30A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	17	-	ns
$t_r$	Turn-on Rise Time		-	49	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	74	-	ns
$t_f$	Turn-off Fall Time		-	26	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	80	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S=30A$	-	-	1.2	V

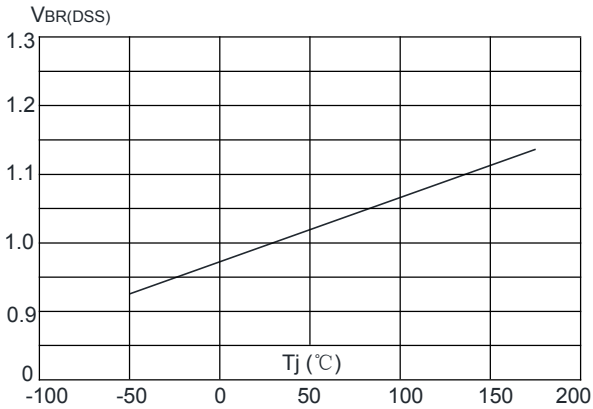
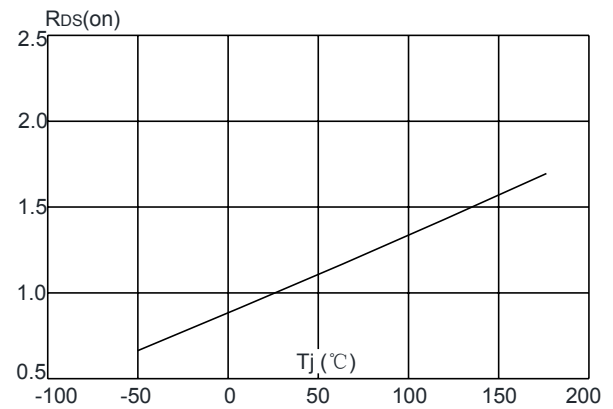
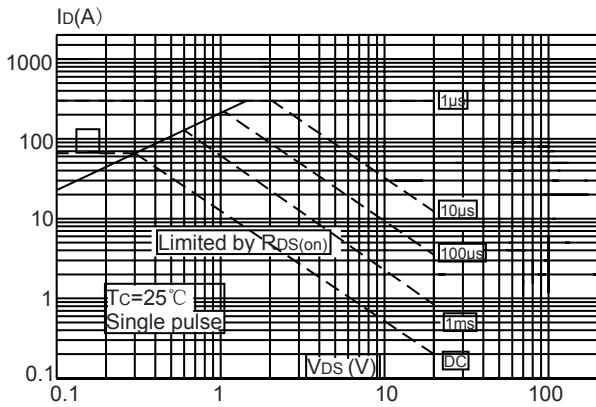
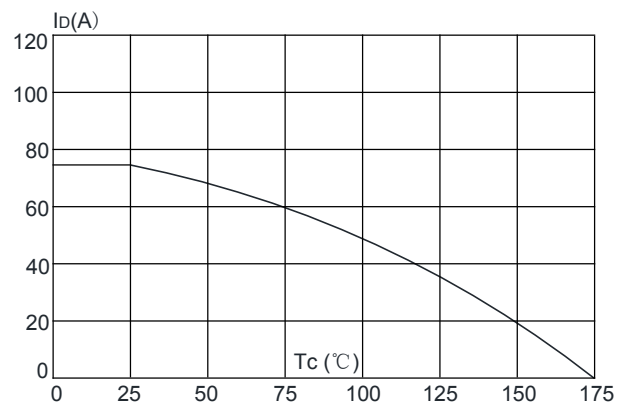
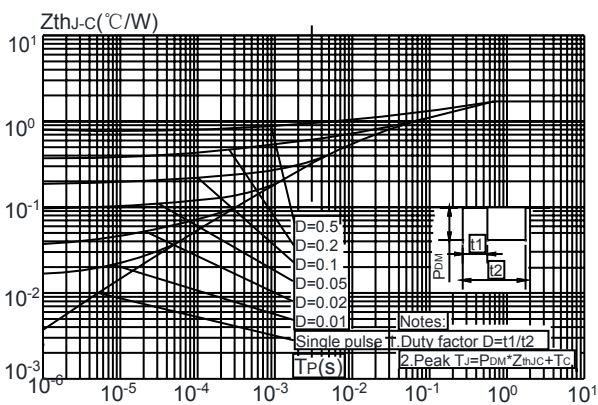
Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

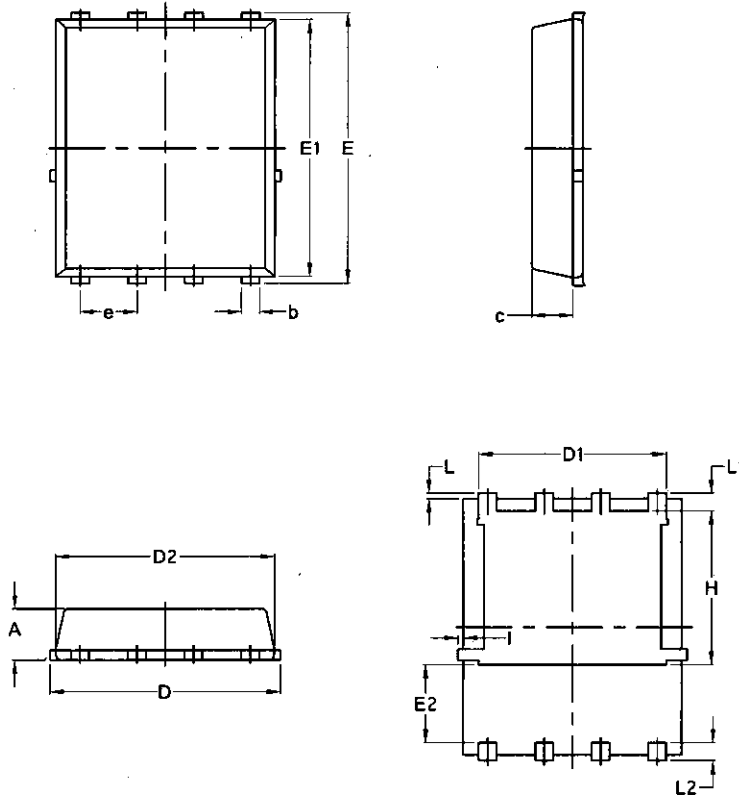
2. EAS condition:  $T_J=25^\circ\text{C}$ ,  $V_{DD}=10V$ ,  $V_G=4.5V$ ,  $L=0.5mH$ ,  $R_G=25\Omega$ ,  $I_{AS}=15A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

## Typical Performance Characteristics

**Figure 1: Output Characteristics**

**Figure 2: Typical Transfer Characteristics**

**Figure 3: On-resistance vs. Drain Current**

**Figure 4: Body Diode Characteristics**

**Figure 5: Gate Charge Characteristics**

**Figure 6: Capacitance Characteristics**


**N-Ch 20V Fast Switching MOSFETs**
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**

**Figure 8: Normalized on Resistance vs. Junction Temperature**

**Figure 9: Maximum Safe Operating Area**

**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**

**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**


**Package Mechanical Data-DFN5\*6-8L-JQ Single**


Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070